

FORM PTO-1449 (REV. 1-84)	U.S. DEPARTMENT OF COMMERCE PATENT & TRADEMARK OFFICE	CASE NO. 7-1	SERIAL NO: 10/164,202
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT: J. M. Hergenrother et al.	
		FILING DATE: June 6, 2002	GROUP: 2812

### U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
	AA 6 1 9 7 6 4 1	3/01	Hergenrother et al.	438	268	—
	AB					
	AC					
	AD					
	AE					
	AF					
	AG					
	AH					
	AI					
	AJ					
	AK					

### FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY/AUTHOR	CLASS	SUB- CLASS	TRANSL' YES NO
	AL					
	AM					
	AN					
	AO					
	AP					

### OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)

Dh	AR	Ishiwara et al., Lateral solid phase epitaxy in selectively P-doped amorphous Si films, Appl. Phys. Lett., Vol. 49, No. 20, p. 1365 (Nov. 1986) (Abstract only)
	AS	Ishiwara et al., Selective Surface Doping Method of P Atoms in Lateral Solid Phase Epitaxy..., Jpn. J. Appl. Phys., Vol. 31, p. 1695 (June 1992)
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	AU	Greene et al., Thin Single Crystal Silicon on Oxide by Lateral Solid Phase Epitaxy of Amorphous Silicon and Silicon Germanium, Mat. Res. Soc. Symp. Proc., Vol. 609, p. A9.31 (2000)
	AV	Choi et al., Ultra-thin-Body SOI MOSFET for Deep-sub-tenth Micron Era, IEEE Electron Dev. Lett., Vol. 21, No. 5, p. 254 (May 2000)
	AW	Subramanian et al, A Bulk-Si-compatible Ultrathin SOI Technology for sub-100nm MOSFETs, Device Research Conf. Tech. Dig., p. 28 (1999)
	AX	Hergenrother et al, The Vertical Replacement-Gate...Gate Length, IEDM Tech. Dig., p. 75 (1999)
	AY	Oh et al, 50 nm Vertical Replacement-Gate (VRG) pMOSFETs, IEDM Tech. Dig., p. 65 (2000)
	AZ	Hergenrother et al, 50 nm Vertical Replacement-Gate (VRG) nMOSFETs with ALD ...Dielectrics, IEDM Tech. Dig., p. 51 (2001)
Dh	BA	Hergenrother et al, The Vertical Replacement-Gate MOSFET, Proc. 2 <sup>nd</sup> European Workshop on the Ultimate Integration of Silicon (ULIS), p. 1 (2001)

EXAMINER: SHEET 1 OF 1 Dh	DATE CONSIDERED: July - 2004
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